

MBT35200MT1

High Current Surface Mount PNP Silicon Switching Transistor for Load Management in Portable Applications

Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	-35	Vdc
Collector-Base Voltage	V _{CBO}	-55	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current - Continuous	I _C	-2.0	Adc
Collector Current - Peak	I _{CM}	-5.0	A
Electrostatic Discharge	ESD	HBM Class 3 MM Class C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D (Note 1)	625 5.0	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 1)	200	°C/W
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D (Note 2)	1.0 8.0	W mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 2)	120	°C/W
Thermal Resistance, Junction-to-Lead #1	R _{θJL}	80	°C/W
Total Device Dissipation (Single Pulse < 10 sec.)	P _{Dsingle} (Notes 2 & 3)	1.75	W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR-4 @ Minimum Pad
2. FR-4 @ 1.0 X 1.0 inch Pad
3. ref: Figure 9

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



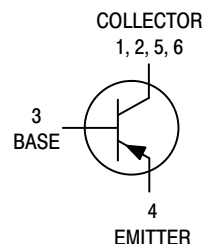
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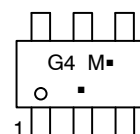
**35 VOLTS
2.0 AMPS
PNP TRANSISTOR**



**CASE 318G
TSOP-6
STYLE 6**



MARKING DIAGRAM



G4 = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MBT35200MT1G	TSOP-6 (Pb-Free)	3,000 / Tape & Reel
SMBT35200MT1G	TSOP-6 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MBT35200MT1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typical	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = -10 mAdc, I _B = 0)	V _{(BR)CEO}	-35	-45	-	Vdc
Collector – Base Breakdown Voltage (I _C = -0.1 mAdc, I _E = 0)	V _{(BR)CBO}	-55	-65	-	Vdc
Emitter – Base Breakdown Voltage (I _E = -0.1 mAdc, I _C = 0)	V _{(BR)EBO}	-5.0	-7.0	-	Vdc
Collector Cutoff Current (V _{CB} = -35 Vdc, I _E = 0)	I _{CBO}	-	-0.03	-0.1	μAdc
Collector – Emitter Cutoff Current (V _{CES} = -35 Vdc)	I _{CES}	-	-0.03	-0.1	μAdc
Emitter Cutoff Current (V _{EB} = -4.0 Vdc)	I _{EBO}	-	-0.01	-0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (Note 1) (I _C = -1.0 A, V _{CE} = -1.5 V) (I _C = -1.5 A, V _{CE} = -1.5 V) (I _C = -2.0 A, V _{CE} = -3.0 V)	h _{FE}	100 100 100	200 200 200	- 400 -	
Collector – Emitter Saturation Voltage (Note 1) (I _C = -0.8 A, I _B = -0.008 A) (I _C = -1.2 A, I _B = -0.012 A) (I _C = -2.0 A, I _B = -0.02 A)	V _{CE(sat)}	- - -	-0.125 -0.175 -0.260	-0.15 -0.20 -0.31	V
Base – Emitter Saturation Voltage (Note 1) (I _C = -1.2 A, I _B = -0.012 A)	V _{BE(sat)}	-	-0.68	-0.85	V
Base – Emitter Turn-on Voltage (Note 1) (I _C = -2.0 A, V _{CE} = -3.0 V)	V _{BE(on)}	-	-0.81	-0.875	V
Cutoff Frequency (I _C = -100 mA, V _{CE} = -5.0 V, f = 100 MHz)	f _T	100	-	-	MHz
Input Capacitance (V _{EB} = -0.5 V, f = 1.0 MHz)	C _{ibo}	-	600	650	pF
Output Capacitance (V _{CB} = -3.0 V, f = 1.0 MHz)	C _{obo}	-	85	100	pF
Turn-on Time (V _{CC} = -10 V, I _{B1} = -100 mA, I _C = -1 A, R _L = 3 Ω)	t _{on}	-	35	-	nS
Turn-off Time (V _{CC} = -10 V, I _{B1} = I _{B2} = -100 mA, I _C = 1 A, R _L = 3 Ω)	t _{off}	-	225	-	nS

1. Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%

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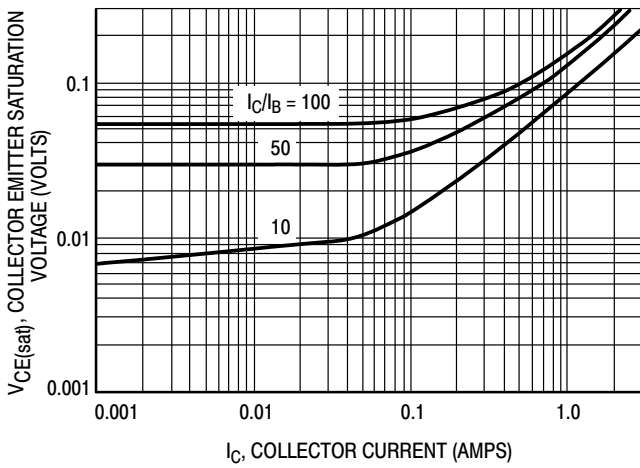


Figure 1. Collector Emitter Saturation Voltage versus Collector Current

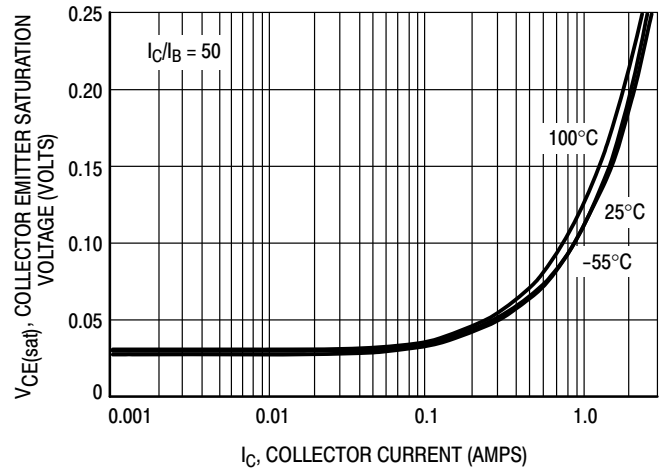


Figure 2. Collector Emitter Saturation Voltage versus Collector Current

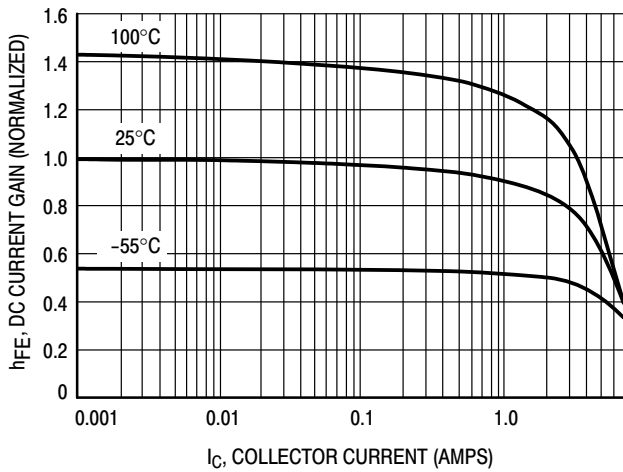


Figure 3. DC Current Gain versus Collector Current

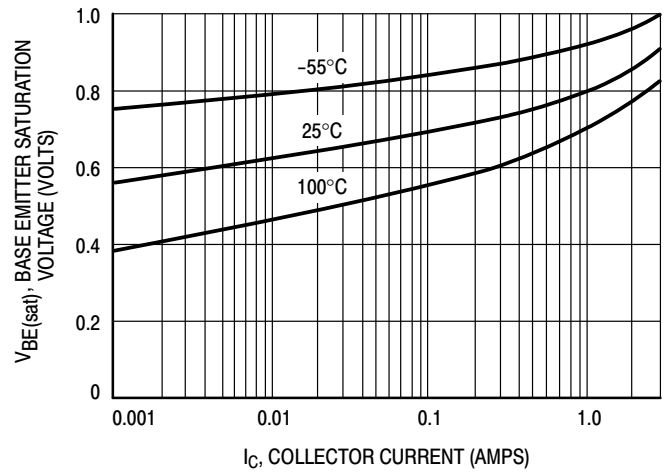


Figure 4. Base Emitter Saturation Voltage versus Collector Current

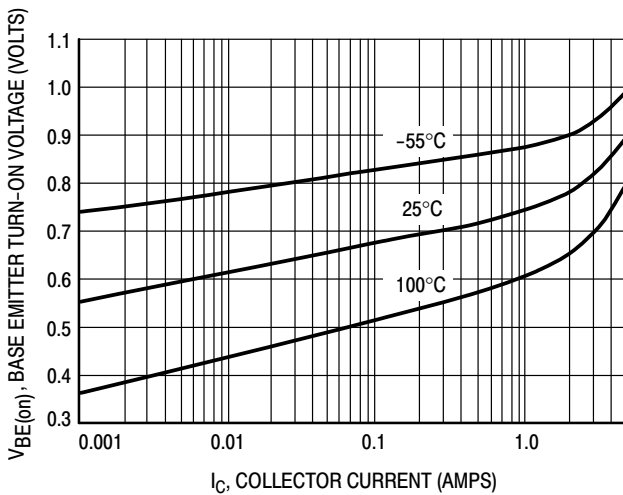


Figure 5. Base Emitter Turn-On Voltage versus Collector Current

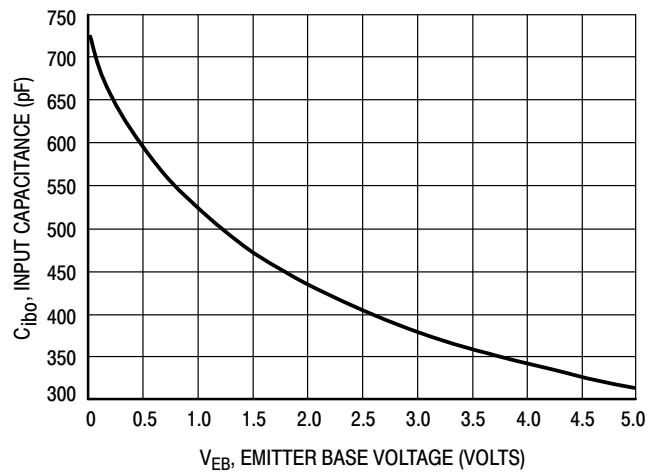


Figure 6. Input Capacitance

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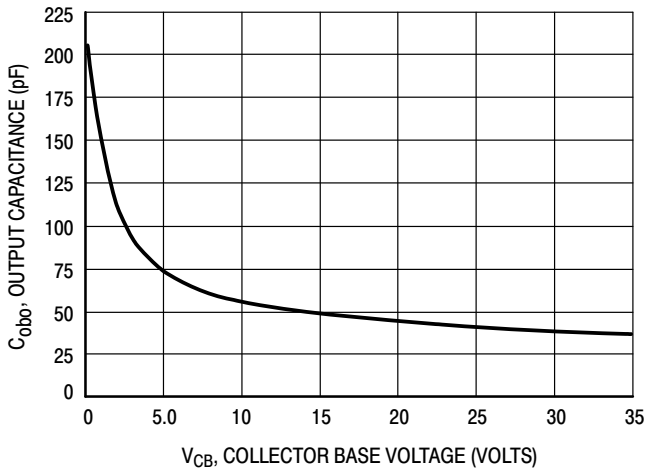


Figure 7. Output Capacitance

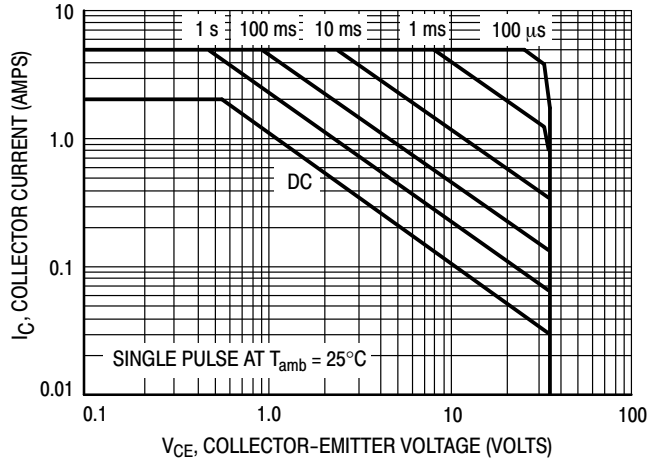


Figure 8. Safe Operating Area

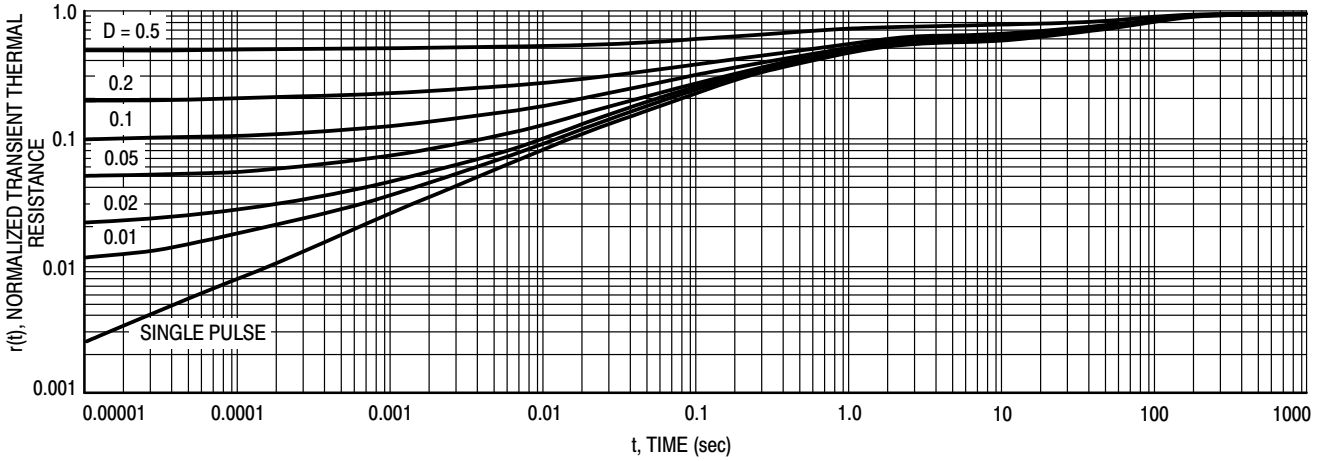


Figure 9. Normalized Thermal Response

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



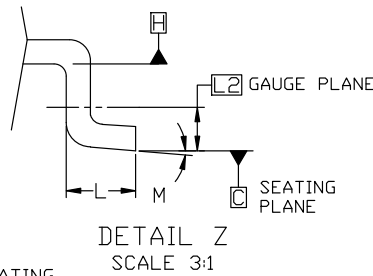
TSOP-6 3.00x1.50x0.90, 0.95P
CASE 318G
ISSUE W

DATE 26 FEB 2024



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN 1 INDICATOR MUST BE LOCATED IN THE INDICATED ZONE



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
A2	0.80	0.90	1.00
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
M	0°	---	10°



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



TSOP-6 3.00x1.50x0.90, 0.95P
CASE 318G
ISSUE W

DATE 26 FEB 2024

GENERIC MARKING DIAGRAM*



IC



STANDARD

XXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb-Free Package

XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:

- PIN 1. DRAIN
- 2. DRAIN
- 3. GATE
- 4. SOURCE
- 5. DRAIN
- 6. DRAIN

STYLE 2:

- PIN 1. EMITTER 2
- 2. BASE 1
- 3. COLLECTOR 1
- 4. EMITTER 1
- 5. BASE 2
- 6. COLLECTOR 2

STYLE 3:

- PIN 1. ENABLE
- 2. N/C
- 3. R BOOST
- 4. Vz
- 5. V in
- 6. V out

STYLE 4:

- PIN 1. N/C
- 2. V in
- 3. NOT USED
- 4. GROUND
- 5. ENABLE
- 6. LOAD

STYLE 5:

- PIN 1. EMITTER 2
- 2. BASE 2
- 3. COLLECTOR 1
- 4. EMITTER 1
- 5. BASE 1
- 6. COLLECTOR 2

STYLE 6:

- PIN 1. COLLECTOR
- 2. COLLECTOR
- 3. BASE
- 4. EMITTER
- 5. COLLECTOR
- 6. COLLECTOR

STYLE 7:

- PIN 1. COLLECTOR
- 2. COLLECTOR
- 3. BASE
- 4. N/C
- 5. COLLECTOR
- 6. EMITTER

STYLE 8:

- PIN 1. Vbus
- 2. D(in)
- 3. D(in)+
- 4. D(out)+
- 5. D(out)
- 6. GND

STYLE 9:

- PIN 1. LOW VOLTAGE GATE
- 2. DRAIN
- 3. SOURCE
- 4. DRAIN
- 5. DRAIN
- 6. HIGH VOLTAGE GATE

STYLE 10:

- PIN 1. D(OUT)+
- 2. GND
- 3. D(OUT)-
- 4. D(IN)-
- 5. VBUS
- 6. D(IN)+

STYLE 11:

- PIN 1. SOURCE 1
- 2. DRAIN 2
- 3. DRAIN 2
- 4. SOURCE 2
- 5. GATE 1
- 6. DRAIN 1/GATE 2

STYLE 12:

- PIN 1. I/O
- 2. GROUND
- 3. I/O
- 4. I/O
- 5. VCC
- 6. I/O

STYLE 13:

- PIN 1. GATE 1
- 2. SOURCE 2
- 3. GATE 2
- 4. DRAIN 2
- 5. SOURCE 1
- 6. DRAIN 1

STYLE 14:

- PIN 1. ANODE
- 2. SOURCE
- 3. GATE
- 4. CATHODE/DRAIN
- 5. CATHODE/DRAIN
- 6. CATHODE/DRAIN

STYLE 15:

- PIN 1. ANODE
- 2. SOURCE
- 3. GATE
- 4. DRAIN
- 5. N/C
- 6. CATHODE

STYLE 16:

- PIN 1. ANODE/CATHODE
- 2. BASE
- 3. EMITTER
- 4. COLLECTOR
- 5. ANODE
- 6. CATHODE

STYLE 17:

- PIN 1. EMITTER
- 2. BASE
- 3. ANODE/CATHODE
- 4. ANODE
- 5. CATHODE
- 6. COLLECTOR

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